

IN THE SPECIFICATION:

Please replace the paragraph beginning on page 2, line 13 and ending on line 17 with the following;

Next, a second reinforcing member 103 to which a ring-shape frame 104 [[is adhered]] is adhered to the other surface of the semiconductor substrate 100 as illustrated in FIG. 4D. The second reinforcing member 103 fixes each semiconductor device chip when, for example, the semiconductor substrate 100 is diced into the respective chips. After that, the first reinforcing member 101 is removed from the semiconductor substrate 100.

Please replace the paragraph beginning on page 4, line 14 and ending on line 27 with the following;

In this way, according to this manufacturing method, the ring-shaped reinforcing member is adhered to the semiconductor substrate whose strength is reduced by thinly processing to prevent ~~occurrence~~ of occurrence of the nick and the crack on the semiconductor substrate. The use of the ring-shaped reinforcing member with the outer diameter equal to that of the semiconductor substrate eliminates the need for changing the transferring unit and cassette according to the dedicated jig, unlike the case, for example, in which the dedicated jig for enhancing strength of the thinly processed semiconductor substrate is used. Moreover, according to this manufacturing method, as an adhering material for adhering the ring-shaped reinforcing member to the semiconductor substrate, a material is used that does not change its state at temperature added thereto when the metallic film is formed. For this reason, under the metallic film forming conditions, the adhering material does not generate gas that is due to its melting and that adversely influences formation of the metallic film. This makes it possible to form electrodes with high reliability.

Please replace the paragraph beginning on page 8, line 13 and ending on line 15 with the following;

An explanation is given of a semiconductor device manufacturing method and a ring-shaped reinforcing member used therein according to this embodiment with reference to FIGS. 1A to 1[[G]] J and FIG. 2.

Please replace the paragraph beginning on page 8, line 26 and ending on page 9, line 5 with the following;

Next, a first tape member 12 is adhered to one surface of the semiconductor substrate 11 with an ultraviolet curable adhesive, a low-tack adhesive, and an organic adhesive such as thermoplastic resin. The first tape member 12 is formed of resin with high heat resistan[[t]]ce, for example, polyethylene terephthalate resin, vinyl chloride resin, and polyolefin resin. The first tape member 12 protects one surface of the semiconductor substrate 11 and prevents occurrence of the nick and the crack on the semiconductor substrate 11 at the time of thinning the semiconductor substrate 11 in a next process.

Please replace the paragraph beginning on page 9, line 7 and ending on page 9, line 14 with the following;

Next, a portion (~~broken line portion in the figure~~) of the semiconductor substrate 11 that is close to the other surface of the semiconductor substrate 11 is removed by back grinding (cutting process) and chemical etching to thin the semiconductor substrate 11 as illustrated in FIG. 1B. For example, a semiconductor substrate with an original thickness of 500 μm is thinned up to 100 μm . Since the semiconductor substrate 11 is reinforced by the first tape member 12 adhered to one surface, occurrence of the nick and the crack by a mechanical stress generated at the time of the thinning process is restrained or prevented.